## MEII-EXTE-REME-may 18

Q. P. Code: 36806

	(3 Hours) Total Marks: 80	,
N.B. :	(1) Question number 1 is compulsory.	S
	(2) Attempt any three questions from remaining questions.	31
	(3) Figures to the right indicate full marks.	131
	(4) Assume suitable data wherever necessary and indicate the same.	131
	(4) Assume suitable data was a second	7
Q. 1	Write a short note on following.	[20]
	(a) Coupled Lines	
	(b) Image Frequency in Mixers	
	(c) Dielectric Resonator Oscillator	
	(d) Properties of S-parameters	1101
Q. 2	(a) Explain Hybrid and Monolithic MIC by comparing the two MICs in the	[10]
	following areas Cost, size and weight, Design flexibility, Circuit tweaking and	
	Reliability.	F101
	(b) What is interference effects and frequency sharing explain.	[10]
Q. 3	(a) Write a short note on Microwave Systems Engineering.	[10]
	(b) The Triquint T1G6000528 GaN HEMT has the following scattering parameters	[10]
	(b) The Triquint T1G6000528 GaN HEM1 has the following scattering parameters at 1.9 GHz ( $Z0 = 50 \Omega$ ):	
	$S11 = 0.869 \angle -159^{\circ}$	
	$S12 = 0.031 \angle -9^{\circ}$	
	S21 = 4.250 ∠ 61°	
	S22 = 0.507 \( \sigma -117\)	
	Determine the stability of this transistor by using the $K-\Delta$ test and the $\mu$ -test,	
	and plot the stability circles on a Smith chart.	
0.4	Design an amplifier to have a gain of 11 dB at 4.0 GHz. Plot constant-gain circle	[20]
X.	for	
	GS = 2 and 3 dB, and $GL = 0$ and 1 dB. Calculate and plot the input return loss	
	and overall amplifier gain from 3 to 5 GHz. The transistor has the following	
	scattering parameters ( $Z0 = 50 \Omega$ ):	
	f(GHz) S11 S12 S21 S22	
	3 0.80∠-90° 0 2.8∠100° 0.66∠ -50°	

	5 0.71∠ -140° 0 2.3∠60° 0.58∠-85	
Q. 5 (a)	For a load impedance $Z_L = 60 - j80 \Omega$ , design single-stub (short circuit) shunt tuning networks to match this load to a 50 $\Omega$ line. Assuming that the load is	[10]

(b) How is Vector Network Analyzer used to measure periodic large signal [10] waveform with all harmonics.

0.75 ∠-120° 0 2.5∠80°

0.60 ∠-70 °

Q. 6 (a) Draw and explain in detail Single-Ended Diode Mixer. [10]

(b) Show that the reflection coefficient is larger than 1 for a load of negative [10] resistance. Justify you answer using I2R relation.